



**DMMT3904W** 

#### 40V MATCHED PAIR NPN SMALL SIGNAL TRANSISTOR IN SOT363

#### **Features**

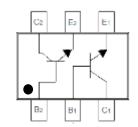
- BVceo > 40V
- I<sub>C</sub> = 200mA High Collector Current
- Pair of NPN Transistors that are Intrinsically Matched (Note 1)
- 2% Matching on Current Gain (hFE)
- 2mV Matching on Base-Emitter Voltage (V<sub>BE</sub>)
- Fully Internally Isolated in a Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 2 & 3)
- Halogen and Antimony Free. "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 5)

#### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)

#### **Applications**

- Current Mirrors
- Differential and Instrumentation Amplifiers
- Comparators



Device Schematic and Pin-Out Top View

#### **SOT363**



Top View

#### Ordering Information (Notes 5 & 6)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMMT3904W-7-F	AEC-Q101	K4A	7	8	3,000
DMMT3904WQ-7-F	Automotive	K4A	7	8	3,000

Notes:

- 1. Intrinsically matched pair as this is built with adjacent die from the same wafer.
- 2. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 3. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 4. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- ${\it 6. For packaging details, go to our website at http://www.diodes.com/products/packages.html.}\\$

#### **Marking Information**

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K4A = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 2 = February)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2	024	2025	2026	2027	2028
Code	Е	F	G	Н		J	K		L	М	N	0	Р
Month	Jan	Feb	Mar	Apr	May	y Ju	n J	lul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6		7	8	9	0	N	D



# Absolute Maximum Ratings (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	Ic	200	mA

# Thermal Characteristics – Total Device (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7) Total Device	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>0JA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

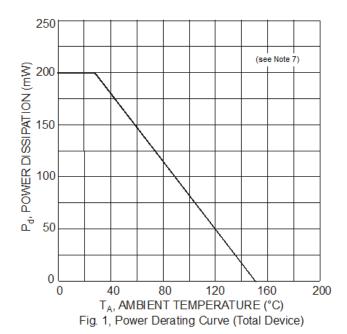
#### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

#### Thermal Characteristics - Total Device



<sup>7.</sup> For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.



# Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS			, ,,	1		1
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	_	_	V	$I_C = 100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage(Note 9)	BV <sub>CEO</sub>	40	_	_	V	$I_C = 1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	_	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I <sub>CEX</sub>	_	_	50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3.0V
Base Cutoff Current	I <sub>BL</sub>	_	_	50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3.0V
ON CHARACTERISTICS (Note 9)					I	
DC Current Gain	hFE	40 70 100 60 30	_	300 — —	_	$I_{C} = 100\mu A, \ V_{CE} = 1.0V$ $I_{C} = 1.0mA, \ V_{CE} = 1.0V$ $I_{C} = 10mA, \ V_{CE} = 1.0V$ $I_{C} = 50mA, \ V_{CE} = 1.0V$ $I_{C} = 100mA, \ V_{CE} = 1.0V$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	_	200 300	mV	$I_C = 10mA$ , $I_B = 1.0mA$ $I_C = 50mA$ , $I_B = 5.0mA$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.65	_	850 950	mV	$I_C = 10mA$ , $I_B = 1.0mA$ $I_C = 50mA$ , $I_B = 5.0mA$
MATCHING CHARACTERISTICS			•			•
DC Current Gain Matching (Note 10)	h <sub>FE1</sub> / h <sub>FE2</sub>	_	1	2	%	$I_C = 2mA$ , $V_{CE} = 5V$
Base-Emitter Voltage Matching (Note 11)	V <sub>BE1</sub> - V <sub>BE2</sub>	_	1	2	mV	$I_C = 2mA$ , $V_{CE} = 5V$
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(SAT)1</sub> / V <sub>CE(SAT)2</sub>	_	1	2	%	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(SAT)1</sub> / V <sub>BE(SAT)2</sub>	_	1	2	%	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
SMALL SIGNAL CHARACTERISTICS						•
Output Capacitance	C <sub>OBO</sub>	_	_	4.0	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	C <sub>IBO</sub>	_	_	8.0	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_C = 0$
Input Impedance	h <sub>IE</sub>	1.0	_	10	kΩ	
Voltage Feedback Ratio	h <sub>RE</sub>	0.5	_	8	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h <sub>FE</sub>	100	_	400	_	f = 1.0kHz
Output Admittance	hoE	1.0	_	40	μS	
Current Gain-Bandwidth Product	f⊤	300	_	_	MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA, f = 100MHz
Noise Figure	NF	_	_	5.0	dB	$V_{CE} = 5.0V$ , $I_{C} = 100\mu A$ , $R_{S} = 1.0k\Omega$ , $f = 1.0kHz$
SWITCHING CHARACTERISTICS			_			
Delay Time	t <sub>D</sub>	_	_	35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Rise Time	t <sub>R</sub>			35	ns	$V_{BE(OFF)} = -0.5V, I_{B1} = 1.0mA$
Storage Time	t <sub>S</sub>	_		200	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA,
Fall Time	t <sub>F</sub>	_	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

Notes:

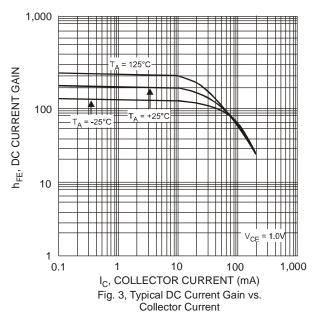
<sup>9.</sup> Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

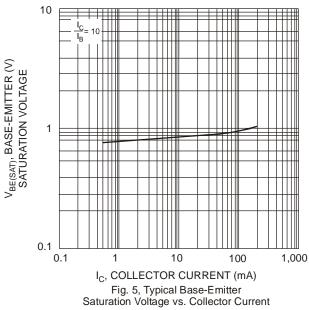
<sup>10.</sup> Is the ratio of one transistor compared to the other transistor.

<sup>11.</sup>  $V_{\text{BE1}}$  -  $V_{\text{BE2}}$  is the absolute difference of one transistor compared to the other transistor.



# Typical Electrical Characteristics (@TA = +25°C unless otherwise specified.)





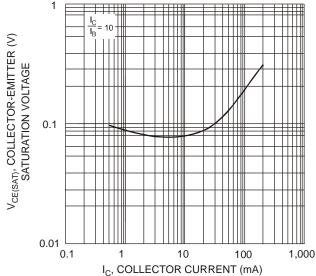
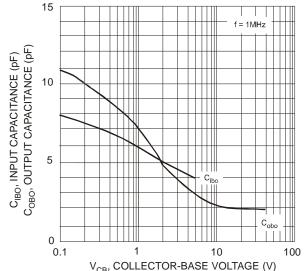


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

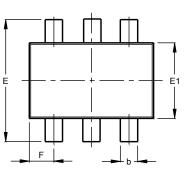


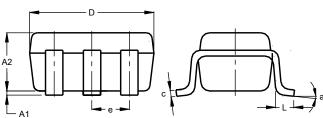
V<sub>CB</sub>, COLLECTOR-BASE VOLTAGE (V) Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.





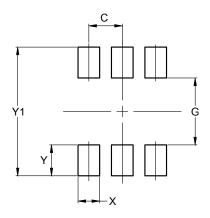
	SOT363						
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	1.00				
b	0.10	0.30	0.25				
C	0.10	0.22	0.11				
D	1.80	2.20	2.15				
E	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е		.650 B	SC				
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**

**SOT363** 



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Υ	0.600
Y1	2.500



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